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List of Publications by Year
in descending order

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96 papers	2,252 citations	218677 26 h-index	243625 44 g-index
96 all docs	96 docs citations	96 times ranked	1000 citing authors

#	Article	IF	Citations
1	Interpreting the nonideal reverse bias C-V characteristics and importance of the dependence of Schottky barrier height on applied voltage. Physica B: Condensed Matter, 1995, 205, 41-50.	2.7	150
2	Parameter extraction from non-ideal Câ^'V characteristics of a Schottky diode with and without interfacial layer. Solid-State Electronics, 1992, 35, 835-841.	1.4	148
3	On the barrier inhomogeneities of polyaniline/p-Si/Al structure at low temperature. Applied Surface Science, 2005, 250, 43-49.	6.1	98
4	Some electrical properties of polyaniline/p-Si/Al structure at 300K and 77K temperatures. Microelectronic Engineering, 2008, 85, 278-283.	2.4	97
5	The bias-dependence change of barrier height of Schottky diodes under forward bias by including the series resistance effect. Physica Scripta, 1996, 53, 118-122.	2.5	93
6	Currentâ€"voltage and capacitanceâ€"voltage characteristics of polypyrrole/p-InP structure. Vacuum, 2005, 77, 269-274.	3.5	90
7	Effect of series resistance on the forward current-voltage characteristics of Schottky diodes in the presence of interfacial layer. Solid-State Electronics, 1996, 39, 83-87.	1.4	89
8	The effects of the temperature on the some parameters obtained from currentâ€"voltage and capacitanceâ€"voltage characteristics of polypyrrole/n-Si structure. Polymer, 2005, 46, 563-568.	3.8	77
9	Determination of the density of Si-metal interface states and excess capacitance caused by them. Physica B: Condensed Matter, 1992, 179, 285-294.	2.7	75
10	High barrier metallic polymer/p-type silicon Schottky diodes. Solid-State Electronics, 1996, 39, 677-680.	1.4	61
11	On the some electrical properties of the non-ideal PPy/p-Si/Al structure. Polymer, 2005, 46, 10982-10988.	3.8	60
12	On the Forward Bias Excess Capacitance at Intimate and MIS Schottky Barrier Diodes with Perfect or Imperfect Ohmic Back Contact. Physica Scripta, 2000, 61, 209-212.	2.5	58
13	Series resistance determination of Au/Polypyrrole/p-Si/Al structure by currentâ€"voltage measurements at low temperatures. Materials Science and Engineering C, 2009, 29, 1486-1490.	7.3	57
14	Temperature-dependent currentâ€"voltage characteristics of the Au/n-InP diodes with inhomogeneous Schottky barrier height. Physica B: Condensed Matter, 2009, 404, 1558-1562.	2.7	49
15	Experimental determination of the laterally homogeneous barrier height of Au/n-Si Schottky barrier diodes. Physica B: Condensed Matter, 2004, 348, 397-403.	2.7	44
16	The temperature dependence of currentâ€"voltage characteristics of the Au/Polypyrrole/p-Si/Al heterojunctions. Journal of Physics Condensed Matter, 2006, 18, 2665-2676.	1.8	44
17	High-barrier height Sn/p-Si schottky diodes with interfacial layer by anodization process. Applied Surface Science, 2001, 172, 1-7.	6.1	42
18	Characterization of capacitanceâ€"frequency features of Sn/polypyrrole/n-Si structure as a function of temperature. Polymer, 2005, 46, 6148-6153.	3.8	35

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19	The effects of the time-dependent on the characteristic parameters of polypyrrole/p-type Si/Al diode. Polymer, 2004, 45, 7335-7340.	3.8	34
20	Effect of thermal annealing in nitrogen on theI - VandC - Vcharacteristics of Cr - Ni - Co alloy/LEC n-GaAs Schottky diodes. Semiconductor Science and Technology, 1997, 12, 1028-1031.	2.0	32
21	Determination of the lateral barrier height of inhomogeneous Au/n-type InP/In Schottky barrier diodes. Semiconductor Science and Technology, 2007, 22, 851-854.	2.0	31
22	Temperature-dependent currentâ€“voltage and capacitanceâ€“voltage characteristics of the Ag/n-InP/In Schottky diodes. Journal of Materials Science: Materials in Electronics, 2009, 20, 105-112.	2.2	31
23	Analysis of the electrical characteristics of Zn/ZnSe/n-Si/Auâ€“Sb structure fabricated using SILAR method as a function of temperature. Journal of Alloys and Compounds, 2010, 506, 388-394.	5.5	30
24	Temperature dependent currentâ€“voltage characteristics of the Cd/CdO/nâ€“Si/Auâ€“Sb structure. Current Applied Physics, 2010, 10, 513-520.	2.4	29
25	Effect of temperature on the capacitanceâ€“frequency and conductanceâ€“voltage characteristics of polyaniline/p-Si/Al MIS device at high frequencies. Microelectronics Reliability, 2012, 52, 1362-1366.	1.7	29
26	The effects of the temperature on currentâ€“voltage characteristics of Sn/polypyrrole/n-Si structures. Synthetic Metals, 2005, 150, 15-20.	3.9	28
27	Deposition and Characterization of CdS, CuS and ZnS Thin Films Deposited by SILAR Method. Acta Physica Polonica A, 2012, 121, 33-35.	0.5	27
28	Determination of the some electronic parameters of nanostructure copper selenide and Cu/Cu3Se2/n-GaAs/In structure. Journal of Alloys and Compounds, 2015, 627, 200-205.	5.5	26
29	Effects of thermal annealing on electrical characteristics of Cd/CdS/n-Si/Auâ€“Sb sandwich structure. Journal of Alloys and Compounds, 2009, 484, 570-574.	5.5	25
30	The effects of the time-dependent and exposure time to air on Au/epilayer n-Si Schottky diodes. EPJ Applied Physics, 1999, 6, 89-94.	0.7	24
31	The effects of the ageing on the characteristic parameters of polyaniline/p-type Si/Al structure. Applied Surface Science, 2004, 230, 404-410.	6.1	24
32	Temperature dependent currentâ€“voltage characteristics of the Zn/ZnO/n-Si/Auâ€“Sb structure with ZnO interface layer grown on n-Si substrate by SILAR method. Microelectronic Engineering, 2011, 88, 3075-3079.	2.4	22
33	ZnS thin film and Zn/ZnS/n-Si/Au-Sb sandwich structure grown with SILAR method and defining the characteristic parameters. Materials Science in Semiconductor Processing, 2011, 14, 28-36.	4.0	21
34	Temperature dependent of electrical characteristics of Au/n-GaAs/In Schottky diode with In2S3 interfacial layer obtained by using spray pyrolysis method. Journal of Alloys and Compounds, 2015, 646, 954-965.	5.5	21
35	Conductance and capacitance-frequency characteristics of polypyrrole/p-type silicon structures. Journal of Polymer Science, Part B: Polymer Physics, 2003, 41, 1334-1338.	2.1	18
36	Reverse bias capacitanceâ€“voltage characteristics of Al/polyaniline/p-Si/Al structure as a function of temperature. Journal of Non-Crystalline Solids, 2008, 354, 4991-4995.	3.1	18

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37	Influence of film thickness on structural and optical properties of ZnS thin films obtained by SILAR method and analysis of Zn/ZnS/nâ€GaAs/In sandwich structure. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 687-693.	1.8	18
38	Thermal treatment of the MIS and intimate Ni/n-LEC GaAs Schottky barrier diodes. Applied Surface Science, 1998, 135, 350-356.	6.1	17
39	Effective atomic numbers of polypyrrole via transmission method in the energy range 15.74â€“40.93keV. Annals of Nuclear Energy, 2008, 35, 432-437.	1.8	17
40	Effects of ageing on the electrical characteristics of Cd/CdS/n-Si/Auâ€“Sb structure deposited by SILAR method. Journal of Physics and Chemistry of Solids, 2011, 72, 1506-1514.	4.0	17
41	The comparison of electrical characteristics of Au/n-InP/In and Au/In2S3/n-InP/In junctions at room temperature. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2015, 193, 61-69.	3.5	17
42	Optimizing quality of lead-free perovskite thin film with anti-solvent engineering and co-doping SnBr2/SnF2; its solar cell performance. Optical Materials, 2020, 110, 110524.	3.6	16
43	CALCULATION OF THE FLUX ASSOCIATED WITH THE ELECTRON'S SPIN ON THE BASIS OF THE MAGNETIC TOP MODEL. International Journal of Modern Physics B, 2002, 16, 607-614.	2.0	15
44	Barrier Height Modification of n-InP Using a Silver Nanoparticles Loaded Graphene Oxide as an Interlayer in a Wide Temperature Range. Journal of Electronic Materials, 2019, 48, 3169-3182.	2.2	15
45	Influences of thermal annealing, the electrolyte pH, and current density on the interface state density distribution of anodic MOS structures. Applied Physics A: Materials Science and Processing, 1997, 65, 33-37.	2.3	14
46	Currentâ€“voltage and capacitanceâ€“voltage characteristics of metallic polymer/InSe(:Er) Schottky contacts. Microelectronic Engineering, 2000, 51-52, 689-693.	2.4	14
47	Using different chemical methods for deposition of copper selenide thin films and comparison of their characterization. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2015, 150, 111-119.	3.9	13
48	Barrier height enhancement by annealing Crî—¸Niî—¸Co alloy Schottky contacts on LEC GaAs. Solid-State Electronics, 1992, 35, 1423-1426.	1.4	11
49	Determination of the Characteristic Parameters of Polyaniline/p-type Si/Al Structures from Current-Voltage Measurements. International Journal of Polymeric Materials and Polymeric Biomaterials, 2005, 54, 805-813.	3.4	11
50	Aging effects on the interface state density obtained from currentâ€“voltage and capacitanceâ€“frequency characteristics of polypyrrole/p-Si/Al structure. Journal of Applied Polymer Science, 2006, 101, 2313-2319.	2.6	11
51	Effect of electron radiation on electrical parameters of Zn/n-Si/Auâ€“Sb and Zn/ZnO/n-Si/Auâ€“Sb diodes. Journal of Radioanalytical and Nuclear Chemistry, 2019, 319, 667-678.	1.5	11
52	Intrinsic Magnetic Flux of the Electron's Orbital and Spin Motion. International Journal of Theoretical Physics, 2006, 45, 1132-1151.	1.2	10
53	Some electrical and structural properties of Cd/CdS/nâ€“Si/Auâ€“Sb sandwich structure. Superlattices and Microstructures, 2012, 52, 416-429.	3.1	10
54	The effects of thermal annealing on the electrical characteristics of Au/nâ€“InP/In diode. Materials Science in Semiconductor Processing, 2014, 28, 121-126.	4.0	10

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55	Effects of surface passivation on capacitance-voltage and conductance-voltage characteristics of Al/p-type Si/Al and Al/V2O5/p-type Si/Al diodes. Journal of Physics and Chemistry of Solids, 2020, 146, 109564.	4.0	10
56	Characteristics of metallic polymer and Au Schottky contacts on cleaved surfaces of InSe(:Er). Solid-State Electronics, 1997, 41, 924-926.	1.4	9
57	Time-dependent of characteristics of Cu/CuS/n-GaAs/In structure produced by SILAR method. Materials Research Bulletin, 2016, 81, 55-62.	5.2	9
58	The protection from the effects of gamma rays of metal-semiconductor diodes by means of ZnO thin interface layer. Radiation Physics and Chemistry, 2019, 165, 108416.	2.8	9
59	Electrical properties of polypyrrole/p-InP structure. Journal of Polymer Science, Part B: Polymer Physics, 2006, 44, 1572-1579.	2.1	8
60	Temperature dependence of currentâ€“voltage characteristics of the Cd/CdS/n-GaAs/In sandwich structure. Journal of Physics and Chemistry of Solids, 2013, 74, 370-376.	4.0	8
61	Influence of anodic passivation on electrical characteristics of Al/p-Si/Al and Al/V2O5/p-Si/Al diodes. Journal of Materials Science: Materials in Electronics, 2017, 28, 7582-7592.	2.2	8
62	Role of Reduced Graphene Oxide-Gold Nanoparticle Composites on Au/Au-RGO/p-Si/Al Structure Depending on Sample Temperature. Journal of Electronic Materials, 2021, 50, 4752-4761.	2.2	8
63	Cr/- and Fe/n-GaAs Schottky diodes: the stable current-voltage characteristic produced by high-temperature annealing. Semiconductor Science and Technology, 1999, 14, 114-117.	2.0	7
64	Investigation of the Electrical Characteristics of Al/p-Si/Al Schottky Diode. Journal of Physics: Conference Series, 2016, 707, 012013.	0.4	7
65	The stability of electrical characteristics of Ti/n-Si/Ag , Ti/n-Si/Cu and Ti/n-Si/AgCu diodes prepared under the same conditions with respect to increasing aging time. Materials Science in Semiconductor Processing, 2017, 68, 186-192.	4.0	7
66	Series resistance calculation for the Metal-Insulator-Semiconductor Schottky barrier diodes. Applied Physics A: Materials Science and Processing, 1996, 62, 269-273.	2.3	7
67	Thermal stability of Cr-Ni-Co alloy Schottky contacts on MBE -GaAs. Semiconductor Science and Technology, 1998, 13, 776-780.	2.0	6
68	Laterally inhomogeneous barrier analysis of identically prepared Cd/CdS/n-Si/Auâ€“Sb structures by SILAR method. Microelectronics Reliability, 2011, 51, 2179-2184.	1.7	6
69	Temperature dependent electrical properties of Cd/CdS/n-Si/Au-Sb structures. Materials Science in Semiconductor Processing, 2015, 30, 658-664.	4.0	6
70	The Effect of Thermal Anealing on the Series Resistance of Nearly Ideal and Ideal Ti/n-GaAs Schottky Diodes. Physica Scripta, 1998, 58, 636-639.	2.5	5
71	A comparative study on theoretical and experimental methods using basic electrical parameters of Au/CNTs/InP/Auâ€“Ge diodes. Journal of Alloys and Compounds, 2020, 824, 153899.	5.5	5
72	Annealing effect on I-V and C-V characteristics of Al/n-InP Schottky diodes at low temperatures. Materials Today: Proceedings, 2021, 46, 6979-6985.	1.8	5

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73	The Absence of Decimalg-Factor in QHE. Physica Status Solidi (B): Basic Research, 2002, 230, 133-142.	1.5	4
74	Conductance and series resistance measurements of polyaniline/p-Si and polypyrrole/InP junction devices. Physica E: Low-Dimensional Systems and Nanostructures, 2012, 46, 38-42.	2.7	4
75	Effects Of the Î³- radiation on the electrical characteristics of the Au/n-Si/Au-Sb Schottky diode. Journal of Physics: Conference Series, 2016, 707, 012018.	0.4	4
76	Calculation from the currentâ€“voltage and capacitanceâ€“voltage measurements of characteristics parameters of Cd/CdS/n-Si/Au-Sb structure with CdS interface layer grown on n-Si substrate by SILAR method. Microelectronic Engineering, 2008, 85, 1831-1835.	2.4	3
77	Temperature dependent electrical characteristics of Zn/ZnSe/n-GaAs/In structure. Journal of Physics: Conference Series, 2016, 707, 012025.	0.4	3
78	The electrical current characteristics of thermally annealed Co/anodic oxide layer/n-GaAs sandwich structures. International Journal of Modern Physics B, 2019, 33, 1950232.	2.0	3
79	Transfer of graphene thin film obtained by PECVD method to Au/p-Si rectifier junction as interfacial layer and analysis of its barrier characteristics depending on sample temperature. Journal of Materials Science: Materials in Electronics, 2022, 33, 14627-14643.	2.2	3
80	The Effects of Growth Parameters on Electrical Characteristics of In2S3/n-InP Junctions with In2S3 Interfacial Layer Obtained by Chemical Spray Pyrolysis Method. Materials Today: Proceedings, 2016, 3, 1262-1270.	1.8	2
81	Analysis of thermal annealing effects of Au-Cu/n-GaAs/In and Ag-Cu/n- GaAs/In Schottky diodes with different ratios Au-Cu and Ag-Cu alloys. Materials Today: Proceedings, 2019, 18, 1918-1926.	1.8	2
82	Effects of Au-Ag and Au-Cu alloy ratios on the temperature dependent current-voltage characteristics of Au-Ag/n-GaAs/In and Au-Cu/n-GaAs/In Schottky diodes. Materials Today: Proceedings, 2019, 18, 1936-1945.	1.8	2
83	The temperature dependence of current-voltage characteristics of CuAuAg/n-Si/Ti Schottky diode. Materials Today: Proceedings, 2021, 46, 6924-6928.	1.8	2
84	Interpretation of the Iâ€“V, Câ€“V and G/Ï‰-V characteristics of the Au/ZnS/n-GaAs/In structure depending on annealing temperature. Physica B: Condensed Matter, 2021, 611, 412801.	2.7	2
85	A critical look at quantum diffusion and some of its interesting aspects. European Physical Journal B, 2007, 59, 69-73.	1.5	1
86	Temperature Dependent Electrical Characteristics Of Cuâˆ•CuSâˆ•n-Siâˆ•Au-Sb Structure Deposited By SILAR Method. AIP Conference Proceedings, 2011, , .	0.4	1
87	The effects of gamma irradiation on electrical characteristics of Zn/ZnO/n-Si/Au-Sb structure. AIP Conference Proceedings, 2018, , .	0.4	1
88	Effects of aging on the electrical properties of Au/n-Si/Ti, Cu/n-Si/Ti and AuCu/n-Si/Ti Schottky diodes. Materials Today: Proceedings, 2021, 46, 6954-6959.	1.8	1
89	On The Experimental Forward Capacitance-Voltage Characteristics of Schottky Barrier Diodes. Journal for Manufacturing Science and Production, 1999, 2, 145-150.	0.1	0
90	The absence of an ideal two dimensionality in QHE. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1493-1496.	0.8	0

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91	Magnetic Superlattice: Localized Magnetostatic Waves and Magnetic Polaritons. Modern Physics Letters B, 2003, 17, 829-839.	1.9	0
92	Effects of ageing on the electrical characteristics of Zn/ZnS/n-GaAs/In structure. Journal of Physics: Conference Series, 2016, 707, 012016.	0.4	0
93	Nanorods/nanostructral vanadium oxide prepared by spray pyrolysis. AIP Conference Proceedings, 2017, , .	0.4	0
94	Nanostructures and Properties of Vanadium Oxide Thin Film Prepared by Spray Pyrolysis Method. Materials Science Forum, 0, 890, 287-290.	0.3	0
95	Analysis of aging time dependent electrical characteristics of AuCu/n-Si/Ti Schottky type diode. AIP Conference Proceedings, 2017, , .	0.4	0
96	Characterization of deposited CdS thin films by Spray Pyrolysis method and used in Cd/CdS/p-Si/Al structure. AIP Conference Proceedings, 2017, , .	0.4	0